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QUAD ±100V 2.5A 5-LEVEL ULTRASOUND PULSER

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The ABLIC Inc. HDL6V5541HF is a quad, five-level RTZ, high-voltage, ultra high-speed pulser. The HDL6V5541HF consists of logic interfaces, level translators, MOSFET gate drive buffers, and high-voltage, high-current MOSFETs.

Functions

• Quad 5-level pulser with 3-input per channel

Features

- 0 to ±100V output voltage
- ±2.5A source and sink peak current for the 1st and 2nd high-voltage pulses (VPP1/VNN1, VPP2/VNN2)
- ±1.0A source and sink peak current for active ground clamp
- 500Ω (±50mA) active ground clamp without blocking diode for anti-leakage (Analog SW type)
- 15V/ns output slew rate
- Up to 100MHz CMOS clock (transparent mode available)
- Symmetrical positive and negative pulse waveforms for low 2nd order harmonic distortion
- 1.8V to 5V CMOS logic interface
- · Noise-cut diodes at each high-voltage output
- Embedded high-voltage clamp diodes
- 4-mode output current control for the 2nd high-voltage rail
- Automatic thermal protection with indicator
- Latch-up free, low crosstalk between channels by SOI CMOS technology
- 64-lead 9x9mm QFN package (RoHS compliant)

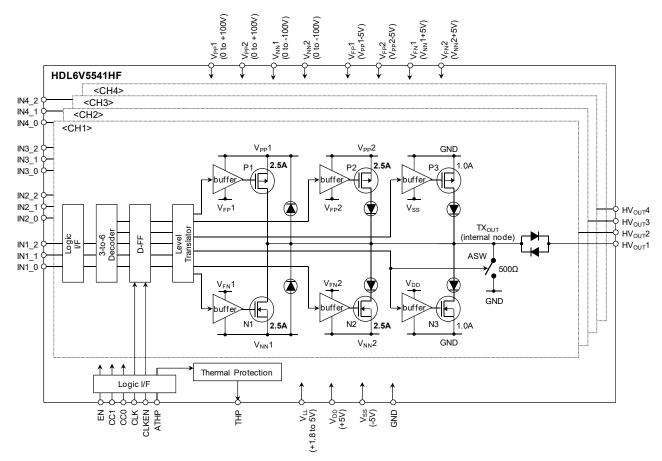


Fig.1 Block diagram

1. Absolute Maximum Ratings

 $T_A=25^{\circ}C$ unless otherwise noted.

Table 1 Absolute Maximum Ratings

No.	Items	Symbol	Value	Units	Condition
1	Logic supply voltage	VLL	-0.4 to +7	V	
2	Positive supply voltage	V_{DD}	-0.4 to +7	V	
3	Negative supply voltage	Vss	-7 to +0.4	V	
4	Positive high-voltage supplies	V _{PP} 1, V _{PP} 2	-0.5 to +105	V	
5	Negative high-voltage supplies	V _{NN} 1, V _{NN} 2	-105 to +0.5	V	
6	Positive high-voltage difference	(V _{PP} 1-V _{PP} 2)	-0.5 to +105	V	INx_[2:0]='001'
			-105 to +105	V	Other than above
7	Negative high-voltage difference	(V _{NN} 1-V _{NN} 2)	-105 to +0.5	V	INx_[2:0]='101'
			-105 to +105	V	Other than above
8	High-voltage outputs (x=1~4)	HV _{оит} х	-105 to +105	V	
9	Gate drive floating voltages	(Vpp1- Vpp1), (Vpp2- Vpp2), (Vpn1- Vnn1), (Vpn2- Vnn2)	-0.4 to +7	V	
10	THP (Thermal Protection) output	THP	-0.4 to +7	V	
11	All Logic input voltages (x=1~4)	INx_[2:0], EN, CLK, CLKEN, CC1, CC0, ATHP	-0.4 to +7	V	
12	Operating junction temperature	T _{Jop}	-20 to +150	°C	
13	Storage temperature	Тѕтс	-55 to +150	°C	
14	Maximum power dissipation	P _{Dmax}	4	W	

NOTE: Stresses beyond the absolute maximum ratings may cause permanent damage to the product.

2. Operating Supply Voltages, Temperature, Logic Inputs, and Power sequencing

2.1 Operating Supply Voltages and Temperature

Table 2 Operating Supply Voltages and Temperature

No	Items	Symbol	Min	Тур	Max	Units	Condition
1	Logic supply voltage	V _{LL}	2.4	2.5 to 5	V_{DD}	V	CLK mode (CLK≤80MHz)
			2.6	2.7 to 5	V_{DD}	V	CLK mode (CLK≤100MHz)
			1.7	1.8 to 5	V_{DD}	٧	TP mode (f _{OUT} ≤20MHz)
			2.4	2.5 to 5	V_{DD}	٧	TP mode (f _{OUT} ≥20MHz)
2	Positive supply voltage	V_{DD}	4.75	5	5.25	V	
3	Negative supply voltage	Vss	-5.25	-5	-4.75	V	
4	Positive high-voltage supplies	Vpp1, Vpp2	0	-	100	V	
5	Negative high-voltage supplies	V _{NN} 1, V _{NN} 2	-100	ı	0	V	
6	Positive high-voltage difference	(V _{PP} 1-V _{PP} 2)	0	ı	100	V	
7	Negative high-voltage difference	(V _{NN} 1-V _{NN} 2)	-100	-	0	V	

No Items Symbol Min Max Units Condition Тур P1 gate drive floating voltage V_{FP}1 V_{PP}1-5.25 **VPP1-5** V_{PP}1-4.75 ٧ 9 P2 gate drive floating voltage $V_{\text{FP}}2$ V_{PP}2-5.25 **Vpp2-5** V_{PP}2-4.75 V_{NN}1+4.75 V_{NN}1+5 V_{NN}1+5.25 10 N1 gate drive floating voltage ٧ $V_{FN}1$ $V_{FN}2$ V_{NN}2+4.75 V_{NN}2+5 V_{NN}2+5.25 ٧ 11 N2 gate drive floating voltage ٧ IC substrate voltage * V_{SUB} 0 V_{PP}x, V_{NN}x slew rate (x=1,2) SRMAX 25 V/ms 14 Operating Free-air Temperature T_A 0 25 75 °C

Table 2 Operating Supply Voltages and Temperature (continued)

NOTE: * The package exposed pad internally connected to the IC substrate must be soldered to the ground.

2.2 Logic Inputs

There are two modes, transparent(TP) and clock(CLK) mode, to deal with the logic inputs INx [2:0] (x=1~4).

TP mode:

Set CLKEN=1, CLK=0. INx_[2:0] are decoded, level-translated, then sent to high-voltage output stage. See table 3 for all the logic inputs.

CLK mode:

Set CLKEN=0. INx_[2:0] are decoded, clocked, level-translated, then sent to high-voltage output stage. See table 3 for all the logic inputs.

No	Items	Symbol	Min	Тур	Max	Units	Condition
1	High-level logic input voltage	V _{IH}	$0.8V_{LL}$	ı	V_{LL}	V	
2	Low-level logic input voltage	VIL	0	ı	0.2V _{LL}	V	
3	Logic input capacitance	Cin	ı	2	-	pF	
4	Logic input high current *1	Іін	-10	ı	10	μA	
5	Logic input low current *2	lıL	-10	ı	10	μA	
6	Logic input pulse width	t _{PW}	10	ı	-	ns	
7	Input rise/fall time	t _r , t _f	ı	1	2.0	ns	10% to 90% CLK, INx_[2:0] CLK mode, CLK≤100MHz
8	Input clock frequency	fclk	i	ı	100	MHz	CLK mode, CLK
9	Duty cycle	D	40	50	60	%	D=τ/T, See Fig.2
10	Data setup time	tsu	0.8	-	-	ns	CLK mode
11	Data hold time	t _{HLD}	2.8	-	-	ns	INx_[2:0], See Fig.2

Table 3 Logic Inputs

NOTE:

^{*1)} ATHP has 50 μ A leak at V_{LL}=2.5V due to 50k Ω internal pull-down resistor.

^{*2)} EN, CC[1:0], and CLKEN have 50 μ A leak at V_{LL}=2.5V due to 50 $k\Omega$ internal pull-up resistor.

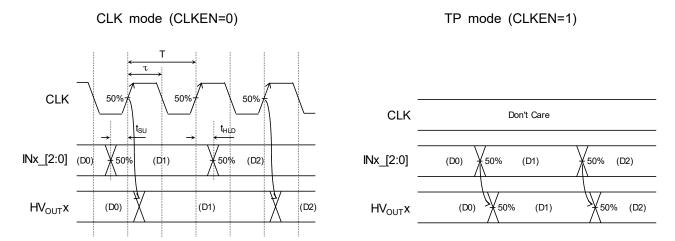


Fig.2 Setup/Hold Time

2.3 Power Supply Sequencing

Table 4 Power Supply Sequencing

Power-Up Sequence

1	VLL
2	V _{DD} , Vss
3	Set EN=1 (HV _{OUT} x=HiZ)
4	(Vpp1-Vpp1), (Vpp2-Vpp2), (Vpn1-Vnn1), (Vpn2-Vnn2)
5	Vpp1, Vpp2, Vnn1, Vnn2
6	Logic control signals

Power-Down Sequence

1	Set EN=1 (HV _{OUT} x=HiZ)
2	Vpp1, Vpp2, Vnn1, Vnn2
3	(Vpp1-Vfp1), (Vpp2-Vfp2), (Vfn1-Vnn1), (Vfn2-Vnn2)
4	V _{DD} , Vss
5	VLL

High-voltage Change Sequence during operation

1	Set EN=1 (HVoutx=HiZ)
2	Change V _{PP} 1, V _{PP} 2, V _{NN} 1, V _{NN} 2
3	Logic control signals

NOTE: It is indispensable to avoid the occurrence of the excessive voltage beyond the maximum rating in applying and cutting of the power supplies.

3. Typical Application Circuit

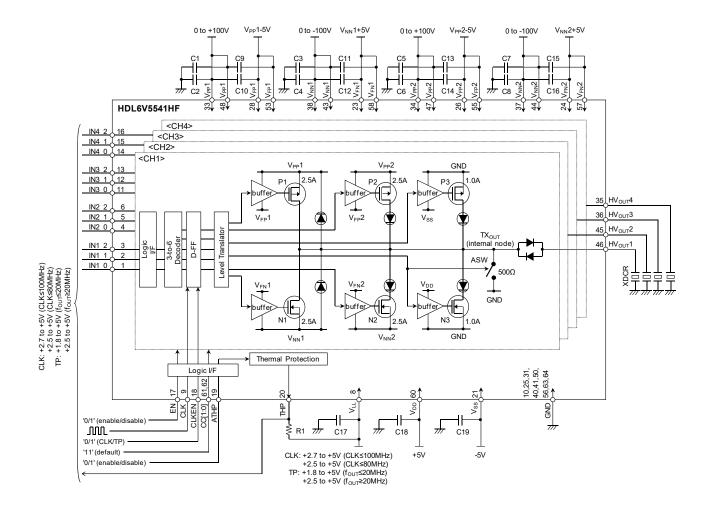


Fig. 3 Typical Application Circuit

NOTE:

- 1. High-voltage power supply pins, V_{PP}x/V_{NN}x (x=1,2), can draw fast transient currents up to ±2.5A. Therefore, ceramic capacitors of ≥200V 0.1μF to 1μF (C1~8) should be connected as close to the pins as possible for bypassing purpose.
- 2. Ceramic capacitors of ≥16V 0.1µF to 1µF (C9~19) also should be connected between high-voltage power supply pins and corresponding floating voltage pins, V_{FP}x/V_{FN}x, and low-voltage power supply pins for bypassing purpose. Connect those as close to the pins as possible.
- 3. It is also important to minimize the trace length and to have enough trace width of those high voltage and floating voltage lines.
- 4. The thermal tab on the bottom of the package must be soldered to the GND.

4. Electrical Characteristics

4.1 Operating Supply Currents

Table 5 Operating Supply Currents

 $\label{eq:VLL} V_{\text{LL}}=2.5\text{V}, \ V_{\text{DD}}=5\text{V}, \ V_{\text{SS}}=-5\text{V}, \ V_{\text{FP}}x=V_{\text{PP}}x-5\text{V}, \ V_{\text{FN}}x=V_{\text{NN}}x+5\text{V}, \ T_{\text{A}}=25^{\circ}\text{C}, \ CLK=100\text{MHz/0(CLKEN=0/1)}, \ ATHP=0, \ HV_{\text{OUT}} \ load=220\text{pF}//200\Omega, \ unless \ otherwise \ specified.$

					Spec				
No.	. Items		Symbol	Min	Тур	Max	Units	Conditions	
_	\/	TP mode		-	0	-	μA	Quiescent current-1	
1	V _{LL} current	CLK mode	Illqd	-	0.7	-	mA	FN 4/D:	
2	V _{DD} current	TP mode	IDDQD	ı	0.7	-	mA	EN=1(Disable) INx [2:0]='000'	
	VDD current	CLK mode		-	12	-	mA	Current mode 4 (CC[1:0]='11')	
3	Vss current		Issqd	-	0.10	-	mA	V _{PP} 1/V _{NN} 1=+/-100V	
4	V _{PP} 1 current		I _{PP1QD}	-	0	-	μΑ	V _{PP} 2/V _{NN} 2=+/-100V	
5	V _{NN} 1 current		I _{NN1QD}	-	0	-	μΑ		
6	V _{PP} 2 current		I _{PP2QD}	-	0.13	-	mA		
7	V _{NN} 2 current		I _{NN2QD}	-	0.10	-	mA		
8	V _{FP} 1 current		I FP1QD	-	0	-	μΑ		
9	V _{FP} 2 current		I _{FP2QD}	-	0.07	-	mA		
10	V _{FN} 1 current	FN1 current		-	0	-	μΑ		
11	V _{FN} 2 current		I _{FN2QD}	-	0.04	-	mA		
12	VLL current	TP mode	Illqe	-	0.06	-	mA	Quiescent current-2	
12	VLL Current	CLK mode	ILLQE	-	0.75	-	mA	EN=0(Enable)	
13	V _{DD} current	TP mode	I _{DDQE}	-	0.7	-	mA	INx [2:0]='000'	
13	VDD current	CLK mode	IDDQE	-	12	-	mA	Current mode 4 (CC[1:0]='11')	
14	Vss current		Issqe	-	0.10	-	mA	V _{PP} 1/V _{NN} 1=+/-100V	
15	V _{PP} 1 current		I _{PP1QE}	-	0	-	μΑ	V _{PP} 2/V _{NN} 2=+/-100V	
16	V _{NN} 1 current		I _{NN1QE}	-	0	-	μΑ		
17	V _{PP} 2 current		I _{PP2QE}	-	0.13	-	mA		
18	V _{NN} 2 current		Inn2qe	-	0.10	-	mA		
19	V _{FP} 1 current		I _{FP1QE}	-	0	-	μA		
20	V _{FP} 2 current		I _{FP2QE}	-	0.07	-	mA		
21	V _{FN} 1 current		I _{FN1QE}	-	0	-	μΑ		
22	V _{FN} 2 current		IFN2QE	-	0.04	-	mA		

Table 5 Operating Supply Currents (continued)

				Spec				0 80	
No.	Iter	ns	Symbol	Min	Тур	Max	Units	Conditions	
-00		TP mode		-	0.06	-	mA	PW Operating current	
23	VLL current	CLK mode	ILLPW	-	0.75	-	mA	EN=0	
24	\/	TP mode		-	2.5	-	mA	Current mode 4 (CC[1:0]='11')	
24	V _{DD} current	CLK mode	IDDPW	-	14	-	mA	4-channel active	
25	Vss current		Isspw	-	2.1	-	mA	Bipolar 3-level 2-cycle	
26	V _{PP} 1 current		I _{PP1PW}	-	2.2	-	mA	f=5MHz, PRT=200µs V _{PP} 1/V _{NN} 1=+/-60V	
27	V _{NN} 1 current		I _{NN1PW}	-	2.5	-	mA	V _{PP} 2/V _{NN} 2=+/-60V	
28	V _{PP} 2 current		I _{PP2PW}	-	0.13	-	mA		
29	V _{NN} 2 current		Inn2pw	-	0.10	-	mA		
30	V _{FP} 1 current		I _{FP1PW}	-	0.08	-	mA		
31	V _{FP} 2 current		I _{FP2PW}	-	0.07	-	mA		
32	V _{FN} 1 current		I _{FN1PW}	-	0.05	-	mA		
33	V _{FN} 2 current		IFN2PW	-	0.04	-	mA		
2.4	\/	TP mode		-	0.25	-	mA	CW Operating current-1	
34	V _{LL} current	CLK mode	ILLCW4	-	1.3	-	mA		
0.5		TP mode	I	-	7	-	mA	EN=0 Current mode 4 (CC[1:0]='11'	
35	V _{DD} current	CLK mode	I _{DDCW4}	-	19	-	mA	4-channel active	
36	Vss current		Isscw4	-	4.8	-	mA	Bipolar 3-level Continuous	
37	V _{PP} 1 current			-	0	-	μA	f=5MHz	
38	V _{NN} 1 current			-	0	-	μA	Vpp1/Vnn1=+/-5V Vpp2/Vnn2=+/-5V	
39	Vpp2 current		IPP2CW4	-	170	-	mA	VPP2/VNN2-+/-3V	
40	V _{NN} 2 current		I _{NN2CW4}	-	158	-	mA		
41	V _{FP} 1 current		I _{FP1CW4}	-	0	-	μA		
42	V _{FP} 2 current		I _{FP2CW4}	-	30	-	mA		
43	V _{FN} 1 current		I _{FN1CW4}	-	0	-	μA		
44	V _{FN} 2 current		I _{FN2CW4}	-	18	-	mA		
45		TP mode		-	0.25	-	mA	CW Operating current-2	
45	V _{LL} current	CLK mode	I _{LLCW3}	-	1.3	-	mA	EN 0	
40		TP mode		-	7.2	-	mA	EN=0 Current mode 3 (CC[1:0]='10')	
46	V _{DD} current	CLK mode	Іррсмз	-	19	-	mA	4-channel active	
47	Vss current		Isscw3	-	5.7	-	mA	Bipolar 3-level Continuous	
48	V _{PP} 1 current		I _{PP1CW3}	-	0	-	μA	f=5MHz	
49	V _{NN} 1 current		Inn1cw3	-	0	-	μA	V _{PP} 1/V _{NN} 1=+/-5V V _{PP} 2/V _{NN} 2=+/-5V	
50	V _{PP} 2 current		I _{PP2CW3}	-	150	-	mA	V PPZ/ V NNZ - 1/-UV	
51	V _{NN} 2 current		I _{NN2CW3}	-	143	-	mA		
52	V _{FP} 1 current		I _{FP1CW3}	-	0	-	μA		
53	V _{FP} 2 current		I _{FP2CW3}	-	22	-	mA		
54			I _{FN1CW3}	-	0	-	μΑ		
55	V _{FN} 2 current		I _{FN2CW3}	-	14	-	mA		

Table 5 Operating Supply Currents (continued)

NI-	14		0		Spec		11	0		
No.	Iter	ทร	Symbol	Min	Тур	Max	Units	Conditions		
		TP mode		-	0.26	-	mA	CW Operating current-3		
56	VLL current	CLK mode	ILLCW2	-	1.3	-	mA			
		TP mode		-	7.2	-	mA	EN=0 Current mode 2 (CC[1:0]='01')		
57	V _{DD} current	CLK mode	I _{DDCW2}	-	19	-	mA	4-channel active		
58	Vss current		Isscw2	-	4.7	-	mA	Bipolar 3-level Continuous		
59	V _{PP} 1 current		I _{PP1CW2}	-	0	-	μA	f=5MHz		
60	V _{NN} 1 current		I _{NN1CW2}	-	0	-	μΑ	V _{PP} 1/V _{NN} 1=+/-5V V _{PP} 2/V _{NN} 2=+/-5V		
61	V _{PP} 2 current		I _{PP2CW2}	-	133	-	mA	V PPZ/ V NNZ - 1/-3 V		
62	V _{NN} 2 current		Inn2cw2	-	130	-	mA			
63	V _{FP} 1 current		I _{FP1CW2}	-	0	-	μA			
64	V _{FP} 2 current V _{FN} 1 current		I _{FP2CW2}	-	15	-	mA			
65			I _{FN1CW2}	-	0	-	μΑ			
66	V _{FN} 2 current		IFN2CW2	-	10	-	mA			
67	V∟∟ current	TP mode	ILLCW1	-	0.31	-	mA	CW Operating current-4		
07	VII current	CLK mode		-	1.4	-	mA	EN=0		
68	V _{DD} current	TP mode	l== a	-	7.2	-	mA	Current mode 1 (CC[1:0]='00')		
00	VDD Current	CLK mode	I _{DDCW1}	-	19	-	mA	4-channel active		
69	Vss current		Isscw1	-	4.7	-	mA	Bipolar 3-level Continuous		
70	V _{PP} 1 current		I _{PP1CW1}	-	0	-	μΑ	f=5MHz		
71	V _{NN} 1 current		I _{NN1CW1}	-	0	-	μΑ	Vpp1/Vnn1=+/-5V Vpp2/Vnn2=+/-5V		
72	V _{PP} 2 current		IPP2CW1	-	111	-	mA			
73	V _{NN} 2 current		I _{NN2CW1}	-	111	-	mA			
74	V _{FP} 1 current		I _{FP1CW1}	-	0	-	μA			
75	V _{FP} 2 current		I _{FP2CW1}	-	7.9	-	mA			
76	V _{FN} 1 current	V _{FN} 1 current		-	0	-	μA			
77	V _{FN} 2 current		I _{FN2CW1}	-	5.3	-	mA			

4.2 Static Characteristics

Table 6 Static Characteristics

 V_{LL} =2.5V, V_{DD} =5V, V_{SS} =-5V, V_{FP} x= V_{PP} x-5V, V_{FN} x= V_{NN} x+5V, T_A =25°C, unless otherwise specified.

NIa	140,000	C. mah al		Spec			Conditions	
No.	Items	Symbol	Min	Тур	Max	Units	Conditions	
1	Output voltage range	HVоитх	-100	-	100	V		
			-	2.5	-	Α	P1 active, V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-60V	
			_	2.5	-	Α	P2 active, V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-60V	
							Current mode 4 (CC[1:0]='11') P2 active, V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-60V	
2	High-side output peak current	Іон	-	1.88	-	Α	Current mode 3 (CC[1:0]='10')	
	The same surpar pour surround		-	1.25	-	Α	P2 active, V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-60V Current mode 2 (CC[1:0]='01')	
			-	0.63	-	Α	P2 active, V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-60V Current mode 1 (CC[1:0]='00')	
3	High-side GND clamp peak current	Іонсь	-	1.0	-	Α	N3 active, V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-60V	
			-	2.5	-	Α	N1 active, V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-60V	
			-	2.5	ı	Α	N2 active, V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-60V Current mode 4 (CC[1:0]='11')	
4	Low-side output peak current	loL	-	1.88	-	Α	N2 active, V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-60V Current mode 3 (CC[1:0]='10')	
			-	1.25	-	Α	N2 active, V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-60V Current mode 2 (CC[1:0]='01')	
			-	0.63	-	Α	N2 active, V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-60V Current mode 1 (CC[1:0]='00')	
5	Low-side GND clamp peak current	lolcl	-	1.0	-	Α	P3 active, V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-60V	
		Ronh	-	9	-	Ω	P1 active, I _{OH} =100mA	
			-	11	-	Ω	P2 active, I _{OH} =100mA Current mode 4 (CC[1:0]='11')	
6	High-side output on-resistance		-	13	-	Ω	P2 active, I _{OH} =100mA Current mode 3 (CC[1:0]='10')	
			-	15	-	Ω	P2 active, I _{OH} =100mA Current mode 2 (CC[1:0]='01')	
			-	23	-	Ω	P2 active, IoH=100mA Current mode 1 (CC[1:0]='00')	
7	High-side GND clamp on-resistance	Ronhcl	-	17	-	Ω	N3 active, I _{OHCL} =100mA	
	-		-	9	-	Ω	N1 active, I _{OL} =100mA	
			-	11	-	Ω	N2 active, I _{OL} =100mA Current mode 4 (CC[1:0]='11')	
8	Low-side output on-resistance	Ronl	-	13	-	Ω	N2 active, I _{OL} =100mA Current mode 3 (CC[1:0]='10')	
			-	15	-	Ω	N2 active, I _{OL} =100mA Current mode 2 (CC[1:0]='01')	
			-	23	-	Ω	N2 active, I _{OL} =100mA Current mode 1 (CC[1:0]='00')	
9	Low-side GND clamp on-resistance	Ronlcl	-	17	ı	Ω	P3 active, I _{OLCL} =100mA	
10	Output off-capacitance	Chvoff	-	10	-	pF	TX _{OUT} x=HiZ	

4.3 Dynamic Characteristics

Table 7 Dynamic Characteristics

 $V_{LL} = 2.5V, \ V_{DD}/V_{SS} = +/-5V, \ V_{FP}X = V_{PP}X - 5V, \ V_{FN}X = V_{NN}X + 5V, \ V_{PP}1/V_{NN}1 = V_{PP}2/V_{NN}2 = +/-60V, \ T_A = 25^{\circ}C, \ CC[1:0] = '11', \ EN = 0, \ ATHP = 0, \ CLK = 100MHz/0 \ (CLKEN = 0/1), \ HV_{OUT} \ load = 220pF//200\Omega, \ unless \ otherwise \ specified.$

					Spec			Conditions	
No.	Items		Symbol	Min	Тур	Max	Units		
1	Output frequency		fout	-	20	-	MHz	Bipolar, TP mode	
		P1/N1		15	-	-		50Ω load	
		drive	SR _{rP-P} ,	4.5	-	ı		220pF//200Ω load	
		P2/N2	SR _{fP-P}	12	-	ı		50Ω load	
2	Output alow rate	drive		3.3	-	-	\ //	220pF//200Ω load	
_	Output slew rate	P1/N1	I/N1	6	-	-	V/ns	50Ω load	
		drive	SR _{r0-P} ,	2	-	-		220pF//200Ω load	
		P2/N2	SR _{f0-P}	6	-	ı		50Ω load	V _{PP} 1/V _{NN} 1=±30V
		drive		2	-	ı		220pF//200Ω load	V _{PP} 2/V _{NN} 2=±30V Bipolar, 1-cyc
		P1/N1		ı	2	-		50Ω load	f _{OUT} =20MHz
2	Output rice time	drive		1	6	ı		220pF//200Ω load	See Fig.4
3	Output rise time	P2/N2	tr	ı	2	ı	ns	50Ω load	1
		drive		ı	6	ı		220pF//200Ω load	
	Output fall time	P1/N1 drive		-	2	-		50Ω load	
4			+,	-	6	-	no	220pF//200Ω load	
4		P2/N2	tf	1	2	ı	ns	50Ω load	
		drive		-	6	-		220pF//200Ω load	
5	Output rise	TP mode	4.	1	56	ı	ns	V _{PP} 1/V _{NN} 1=±30V V _{PP} 2/V _{NN} 2=±30V	
5	propagation delay	CLK mode	t _{dr}	1	61	ı	ns		
6	Output fall	TP mode	+	ı	56	ı	ns	Bipolar, 1-cyc f _{o∪т} =20MHz	
0	propagation delay	CLK mode	t _{df}	ı	61	ı	ns		
7	Output rise	TP mode	+	ı	56	-	ns	See Fig.4	
	propagation delay clamp	CLK mode	t _{drCL}	1	61	ı	ns		
8	Output fall	TP mode	+	ı	56	ı	ns		
0	propagation delay clamp	CLK mode	t _{dfCL}	ı	61	-	ns		
9	Propagation delay match	ing	Δt_{d}	-	±1	±3	ns	1	
10	Second harmonic distorti	on	HD2	-	-40	-	dBc	Bipolar, 2-cyc, f _{OUT} =	5MHz
11	Dulco concollation		HDPC	1	-40	ı	dBc	See Fig.5	
11	Pulse cancellation		HDPC2	1	-40	-	dBc		
12	RMS output jitter	tJ	-	10	-	ps	Bipolar CW, f _{OUT} =5MHz V _{PP} 1/V _{NN} 1=V _{PP} 2/V _{NN} 2=+/-5V		
13	Output enable time	t _{EN}	1	61	-	ns	See Fig.6		
14	Output disable time	tos	ı	61	-	ns			
15	Clock mode enable time		tclken	-	61	-	ns		
16	Clock mode disable time		tclkds	-	61	-	ns		

4.4 Integrated Peripheral Circuits Characteristics

Analog Switch

Table 8 Analog Switch Characteristics

T_A=25°C

NI-	lto man	Curahal		Spec		l luita	Conditions	
No.	Items	Symbol	Min	Тур	Max	Units	Conditions	
1	ASW on-resistance	Ronasw	-	500	-	Ω		

HV Blocking Diode

Table 9 Output HV Blocking Diode Characteristics

T_A=25°C

NIa	ltomo	C) made al	Spec			l luita	Conditions	
No.	Items	Symbol	Min	Тур	Max	Units	Conditions	
1	Forward voltage	V _{FDHV}	-	1.0	-	V	I _F =100mA	
2	Reverse voltage	V_{RDHV}	200	-	ı	V	I _R =1µA	

LV Noise-cut Diode

Table 10 Output LV Noise-cut Diode Characteristics

T_A=25°C

NI-	H	0	Spec			1.1	0 199	
No.	Items	Symbol	Min	Тур	Max	Units	Conditions	
1	Forward voltage	VFDNC	-	0.85	-	V	I==100mA	

Thermal Protection

Table 11 Thermal Protection Characteristics

 $V_{\text{LL}}\text{=}2.5\text{V},~V_{\text{DD}}/V_{\text{SS}}\text{=+/-5V},~T_{\text{A}}\text{=}25^{\circ}\text{C},~\text{unless otherwise specified}.$

N1 -	14	0		Spec		11	Conditions	
No.	Items	Symbol	Min	Тур	Max	Units		
1	THP pull-up voltage	V _{PUTHP}	-	-	5.25	V	Open drain	
2	THP output current	I _{THP}	ı	1.0	-	mA		
3	THP output low voltage	VOLTHP	ı	ı	1.0	V	THP active, VLL=3.3V, ITHP=1mA	
4	THP temperature threshold	T_THP	90	110	130	°C		
5	THP reset hysteresis	THYSTHP	-	10	-	°C		

5. Switching Time Diagram

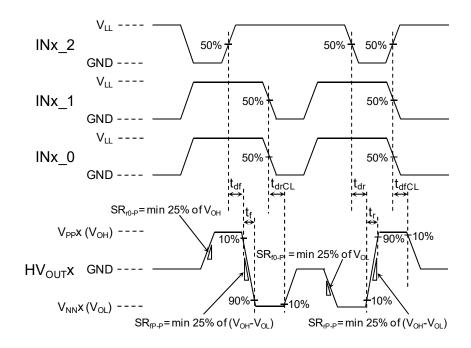
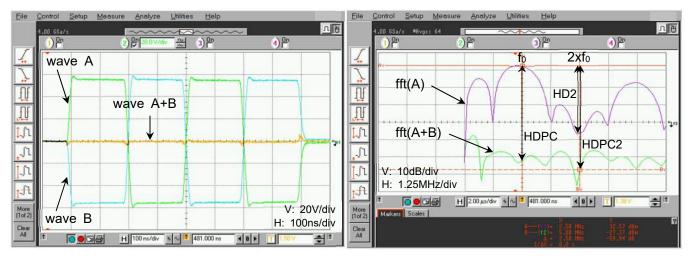


Fig. 4 Propagation delay and Output rise/fall time



Example waveforms: VPP/VNN=+/-60V, f_0 =2.5MHz, 2-cycle, HV_{OUT} load=220pF//200 Ω

Fig.5 2nd harmonic distortion and Pulse cancellation

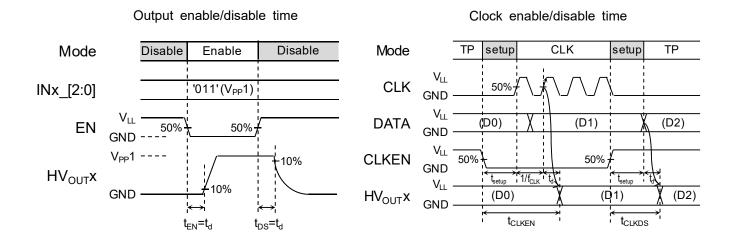


Fig.6 Output enable/disable and Clock enable/disable time

6. Truth Table and Current Mode Control

6.1 Truth Table

Table 12 Truth table

	Logic	Inputs			Output state						
EN	INx_2	INx_1	INx_0	P1	N1	P2	N2	P3	N3	ASW	TX _{OUT} x
				+HV1	-HV1	+HV2	-HV2	GND	GND	GND	(internal node)
0	0	0	0	OFF	OFF	OFF	OFF	OFF	OFF	OFF	HiZ
0	0	0	1	OFF	OFF	ON	OFF	OFF	OFF	OFF	+HV2
0	0	1	0	OFF	OFF	OFF	OFF	OFF	OFF	OFF	HiZ
0	0	1	1	ON	OFF	OFF	OFF	OFF	OFF	OFF	+HV1
0	1	0	0	OFF	OFF	OFF	OFF	ON	ON	ON	GND
0	1	0	1	OFF	OFF	OFF	ON	OFF	OFF	OFF	-HV2
0	1	1	0	OFF	OFF	OFF	OFF	ON	ON	ON	GND
0	1	1	1	OFF	ON	OFF	OFF	OFF	OFF	OFF	-HV1
1	Х	Х	Х	OFF	OFF	OFF	OFF	OFF	OFF	OFF	HiZ

NOTE:

- V_{PP}1/ V_{NN}1=+/-HV1, V_{PP}2/ V_{NN}2=+/-HV2
- x=1~4

6.2 Current Mode Control

Table 13 P2/N2 Drive current mode control

-			lout	[A]
Current Mode	CC1	CC0	P2	N2
1	0	0	0.63	0.63
2	0	1	1.25	1.25
3	1	0	1.88	1.88
4	1	1	2.5	2.5

NOTE:

Recommended mode is as follows:

- Current mode 3 or 4 for high-amplitude short-cycle pulse waveforms, or for driving heavy load
- Current mode 1 or 2 for low-amplitude long pulse train waveforms (e.g. CW), or for driving light load

7. Pin Configuration

Table 14 Pin Configuration

Pin#	Pin Name	I/O	Function
1	IN1_0	ı	Input logic control of the least significant bit of channel 1, HV2 control
2	IN1_1	I	Input logic control of 2nd significant bit of channel 1, HV1 control
3	IN1_2	I	Input logic control of the most significant bit of channel 1, polarity control
4	IN2_0	I	Input logic control of the least significant bit of channel 2, HV2 control
5	IN2_1	I	Input logic control of 2nd significant bit of channel 2, HV1 control
6	IN2_2	I	Input logic control of the most significant bit of channel 2, polarity control
7	NC	-	No connection
8	VLL	-	Positive voltage supply of low voltage interface (+3.3V)
9	CLK	I	Clock Input (100MHz)
10	GND	-	Drive power ground (0V)
11	IN3_0	I	Input logic control of the least significant bit of channel 3, HV2 control
12	IN3_1	I	Input logic control of 2nd significant bit of channel 3, HV1 control
13	IN3_2	I	Input logic control of the most significant bit of channel 3, polarity control
14	IN4_0	I	Input logic control of the least significant bit of channel 4, HV2 control
15	IN4_1	I	Input logic control of 2nd significant bit of channel 4, HV1 control
16	IN4_2	I	Input logic control of the most significant bit of channel 4, polarity control
17	EN	I	Control of drive output enable, Hi=off, Low=on (50kΩ internal pull-up resistor)
18	CLKEN	I	Control of clock enable, Hi=clock disable, Low=clock enable (50kΩ internal pull-up resistor)
19	ATHP		Control of active THP enable, Hi=disable, Low=enable (50kΩ internal pull-down resistor)
20	THP	0	Thermal protection output, open N-MOS drain
21	VSS	ı	Negative low voltage power supply (-5V)
22	NC	ı	No connection
23	VFN1	ı	N-MOS (N1) floating gate drive power supply (VNN1+5V)
24	VFN2	ı	N-MOS (N2) floating gate drive power supply (VNN2+5V)
25	GND	•	Drive power ground (0V)
26	VFP2	ı	P-MOS (P2) floating gate drive power supply (VPP2-5V)
27	NC	ı	No connection
28	VFP1	ı	P-MOS (P1) floating gate drive power supply (VPP1-5V)
29	NC	-	No connection
30	NC	-	No connection
31	GND	ı	Drive power ground (0V)
32	NC	-	No connection

Table 14 Pin Configuration (continued)

33 VPP1 - Positive high voltage power supply 1 for channel 3.4 (0 to +100V) 34 VPP2 - Positive high voltage power supply 2 for channel 3.4 (0 to +100V, VPP2 <vpp1)< td=""> 35 HVOUT4 O Output high voltage for channel 3 36 HVOUT3 O Output high voltage for channel 3 37 VNN1 - Negative high voltage power supply 2 for channel 3.4 (0 to -100V, VNN2>VNN1) 38 VNN1 - Negative high voltage power supply 1 for channel 3.4 (0 to -100V) 40 GND - Drive power ground (0V) 41 GND - Drive power ground (0V) 42 NC - No connection 43 VNN1 - Negative high voltage power supply 1 for channel 1,2 (0 to -100V) 44 VNN2 - Negative high voltage power supply 2 for channel 1,2 (0 to -100V, VNN2>VNN1) 45 HVOUT2 O Output high voltage power supply 2 for channel 1,2 (0 to +100V) 46 HVOUT1 O Output high voltage power supply 2 for channel 1,2 (0 to +100V) 48 VPP1 - Positive</vpp1)<>	Pin#	Pin Name	I/O	Function
35	33	VPP1	ı	Positive high voltage power supply 1 for channel 3,4 (0 to +100V)
36	34	VPP2	-	Positive high voltage power supply 2 for channel 3,4 (0 to +100V, VPP2 <vpp1)< td=""></vpp1)<>
37 VNN2 - Negative high voltage power supply 2 for channel 3.4 (0 to -100V, VNN2>VNN1) 38 VNN1 - Negative high voltage power supply 1 for channel 3.4 (0 to -100V) 39 NC - No connection 40 GND - Drive power ground (0V) 41 GND - Drive power ground (0V) 42 NC - No connection 43 VNN1 - Negative high voltage power supply 1 for channel 1,2 (0 to -100V) 44 VNN2 - Negative high voltage power supply 2 for channel 1,2 (0 to -100V, VNN2>VNN1) 45 HVOUT2 O Output high voltage for channel 2 46 HVOUT1 O Output high voltage power supply 2 for channel 1,2 (0 to -100V, VNN2>VNN1) 47 VPP2 - Positive high voltage power supply 2 for channel 1,2 (0 to +100V) 48 VPP1 - Positive high voltage power supply 1 for channel 1,2 (0 to +100V) 49 NC - No connection 50 GND - Drive power ground (0V) 51 NC - No connection 52 NC - No connection 53 VFP1 - P-MOS (P1) floating gate drive power supply (VPP1-5V) 54 NC - No connection 55 VFP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) 56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor)	35	HVOUT4	0	Output high voltage for channel 4
38 VNN1	36	HVOUT3	0	Output high voltage for channel 3
NC	37	VNN2	-	Negative high voltage power supply 2 for channel 3,4 (0 to -100V, VNN2>VNN1)
40 GND - Drive power ground (0V) 41 GND - Drive power ground (0V) 42 NC - No connection 43 VNN1 - Negative high voltage power supply 1 for channel 1,2 (0 to -100V) 44 VNN2 - Negative high voltage power supply 2 for channel 1,2 (0 to -100V, VNN2>VNN1) 45 HVOUT2 O Output high voltage for channel 2 46 HVOUT1 O Output high voltage for channel 1 47 VPP2 - Positive high voltage power supply 2 for channel 1,2 (0 to +100V) 48 VPP1 - Positive high voltage power supply 1 for channel 1,2 (0 to +100V) 49 NC - No connection 50 GND - Drive power ground (0V) 51 NC - No connection 52 NC - No connection 53 VFP1 - P-MOS (P1) floating gate drive power supply (VPP1-5V) 54 NC - No connection 55 VFP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) 56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 Control of drive current mode 0 (50KΩ internal pull-up resistor) 62 CC1 Control of drive current mode 1 (50KΩ internal pull-up resistor)	38	VNN1	-	Negative high voltage power supply 1 for channel 3,4 (0 to -100V)
41 GND - Drive power ground (0V) 42 NC - No connection 43 VNN1 - Negative high voltage power supply 1 for channel 1,2 (0 to -100V) 44 VNN2 - Negative high voltage power supply 2 for channel 1,2 (0 to -100V, VNN2>VNN1) 45 HVOUT2 O Output high voltage for channel 2 46 HVOUT1 O Output high voltage for channel 1 47 VPP2 - Positive high voltage power supply 2 for channel 1,2 (0 to +100V) 48 VPP1 - Positive high voltage power supply 1 for channel 1,2 (0 to +100V) 49 NC - No connection 50 GND - Drive power ground (0V) 51 NC - No connection 52 NC - No connection 53 VFP1 - P-MOS (P1) floating gate drive power supply (VPP1-5V) 54 NC - No connection 55 VFP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) 56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN2+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50KΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50KΩ internal pull-up resistor)	39	NC	-	No connection
VNN1	40	GND	-	Drive power ground (0V)
VNN1 - Negative high voltage power supply 1 for channel 1,2 (0 to -100V) VNN2 - Negative high voltage power supply 2 for channel 1,2 (0 to -100V, VNN2>VNN1) VNN2 - Negative high voltage for channel 2 HVOUT1 O Output high voltage for channel 2 Fostitive high voltage for channel 1 VPP2 - Positive high voltage power supply 2 for channel 1,2 (0 to +100V) VPP1 - Positive high voltage power supply 1 for channel 1,2 (0 to +100V) VPP1 - No connection NC - No connection NC - No connection VPP1 - P-MOS (P1) floating gate drive power supply (VPP1-5V) NC - No connection VPP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) GND - Drive power ground (0V) VPP2 - P-MOS (N2) floating gate drive power supply (VPP2-5V) NC - No connection VPP1 - N-MOS (N2) floating gate drive power supply (VNN2+5V) NC - N-MOS (N1) floating gate drive power supply (VNN1+5V) NC - No connection VPN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) NC - No connection CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) Drive power ground (0V)	41	GND	-	Drive power ground (0V)
44 VNN2 - Negative high voltage power supply 2 for channel 1,2 (0 to -100V, VNN2>VNN1) 45 HVOUT2 O Output high voltage for channel 2 46 HVOUT1 O Output high voltage for channel 1 47 VPP2 - Positive high voltage power supply 2 for channel 1,2 (0 to +100V) 48 VPP1 - Positive high voltage power supply 1 for channel 1,2 (0 to +100V) 49 NC - No connection 50 GND - Drive power ground (0V) 51 NC - No connection 52 NC - No connection 53 VFP1 - P-MOS (P1) floating gate drive power supply (VPP1-5V) 54 NC - No connection 55 VFP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) 56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor)	42	NC	-	No connection
HVOUT1 O Output high voltage for channel 2 HVOUT1 O Output high voltage for channel 1 VPP2 - Positive high voltage power supply 2 for channel 1,2 (0 to +100V) RVP1 - Positive high voltage power supply 1 for channel 1,2 (0 to +100V) NC - No connection NC - No connection	43	VNN1	-	Negative high voltage power supply 1 for channel 1,2 (0 to -100V)
46 HVOUT1 O Output high voltage for channel 1 47 VPP2 - Positive high voltage power supply 2 for channel 1,2 (0 to +100V) 48 VPP1 - Positive high voltage power supply 1 for channel 1,2 (0 to +100V) 49 NC - No connection 50 GND - Drive power ground (0V) 51 NC - No connection 52 NC - No connection 53 VFP1 - P-MOS (P1) floating gate drive power supply (VPP1-5V) 54 NC - No connection 55 VFP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) 56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	44	VNN2	-	Negative high voltage power supply 2 for channel 1,2 (0 to -100V, VNN2>VNN1)
VPP2 - Positive high voltage power supply 2 for channel 1,2 (0 to +100V) VPP1 - Positive high voltage power supply 1 for channel 1,2 (0 to +100V) VPP1 - Positive high voltage power supply 1 for channel 1,2 (0 to +100V) NC - No connection Drive power ground (0V) NC - No connection NC - No connection NC - No connection VPP1 - P-MOS (P1) floating gate drive power supply (VPP1-5V) NC - No connection VPP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) GND - Drive power ground (0V) VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) N-MOS (N1) floating gate drive power supply (VNN1+5V) NC - No connection NO VPN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) NC - No connection CO VDD - Positive low voltage power supply (+5V) CC1 I Control of drive current mode 0 (50kΩ internal pull-up resistor) CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) Drive power ground (0V)	45	HVOUT2	0	Output high voltage for channel 2
48 VPP1 - Positive high voltage power supply 1 for channel 1,2 (0 to +100V) 49 NC - No connection 50 GND - Drive power ground (0V) 51 NC - No connection 52 NC - No connection 53 VFP1 - P-MOS (P1) floating gate drive power supply (VPP1-5V) 54 NC - No connection 55 VFP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) 56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	46	HVOUT1	0	Output high voltage for channel 1
NC No connection	47	VPP2	-	Positive high voltage power supply 2 for channel 1,2 (0 to +100V)
SO GND - Drive power ground (0V) 51 NC - No connection 52 NC - No connection 53 VFP1 - P-MOS (P1) floating gate drive power supply (VPP1-5V) 54 NC - No connection 55 VFP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) 56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	48	VPP1	-	Positive high voltage power supply 1 for channel 1,2 (0 to +100V)
S1 NC - No connection 52 NC - No connection 53 VFP1 - P-MOS (P1) floating gate drive power supply (VPP1-5V) 54 NC - No connection 55 VFP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) 56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	49	NC	-	No connection
S2 NC - No connection 53 VFP1 - P-MOS (P1) floating gate drive power supply (VPP1-5V) 54 NC - No connection 55 VFP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) 56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	50	GND	-	Drive power ground (0V)
53 VFP1 - P-MOS (P1) floating gate drive power supply (VPP1-5V) 54 NC - No connection 55 VFP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) 56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	51	NC	-	No connection
54 NC - No connection 55 VFP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) 56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	52	NC	-	No connection
55 VFP2 - P-MOS (P2) floating gate drive power supply (VPP2-5V) 56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	53	VFP1	-	P-MOS (P1) floating gate drive power supply (VPP1-5V)
56 GND - Drive power ground (0V) 57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	54	NC	ı	No connection
57 VFN2 - N-MOS (N2) floating gate drive power supply (VNN2+5V) 58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	55	VFP2	ı	P-MOS (P2) floating gate drive power supply (VPP2-5V)
58 VFN1 - N-MOS (N1) floating gate drive power supply (VNN1+5V) 59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	56	GND	ı	Drive power ground (0V)
59 NC - No connection 60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	57	VFN2	-	N-MOS (N2) floating gate drive power supply (VNN2+5V)
60 VDD - Positive low voltage power supply (+5V) 61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	58	VFN1	-	N-MOS (N1) floating gate drive power supply (VNN1+5V)
61 CC0 I Control of drive current mode 0 (50kΩ internal pull-up resistor) 62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	59	NC	-	No connection
62 CC1 I Control of drive current mode 1 (50kΩ internal pull-up resistor) 63 GND - Drive power ground (0V)	60	VDD	-	Positive low voltage power supply (+5V)
63 GND - Drive power ground (0V)	61	CC0	I	Control of drive current mode 0 (50kΩ internal pull-up resistor)
	62	CC1	I	Control of drive current mode 1 (50kΩ internal pull-up resistor)
64 GND - Drive power ground (0V)	63	GND	-	Drive power ground (0V)
	64	GND	-	Drive power ground (0V)

8. Package Outline

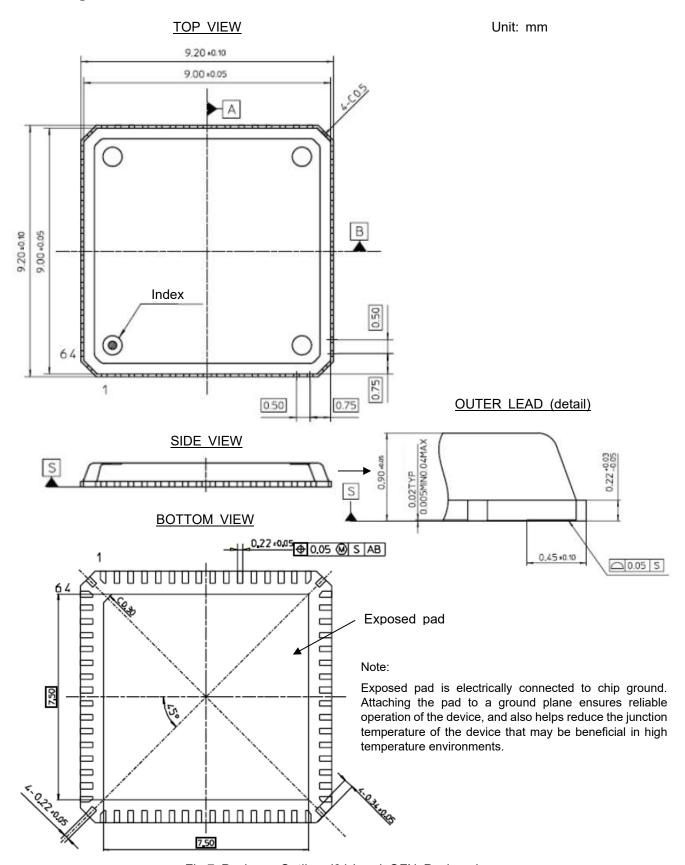
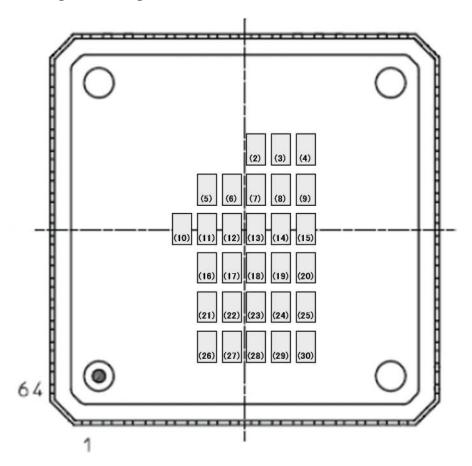


Fig.7 Package Outline (64-Lead QFN Package)

9. Package Marking



No.	Code
(2)	Year sealed : the last one digit of the year
(3)	Month sealed: A~M (exc "l") in the order of Jan. to Dec.
(4)	Week sealed : 1~5
(5)~(15)	HDL6V5541HF (product name)
(16)~(25)	Quality control code
(26)~(30)	Country of origin

Fig.8 Package Marking

10. Transport Media, Quantity

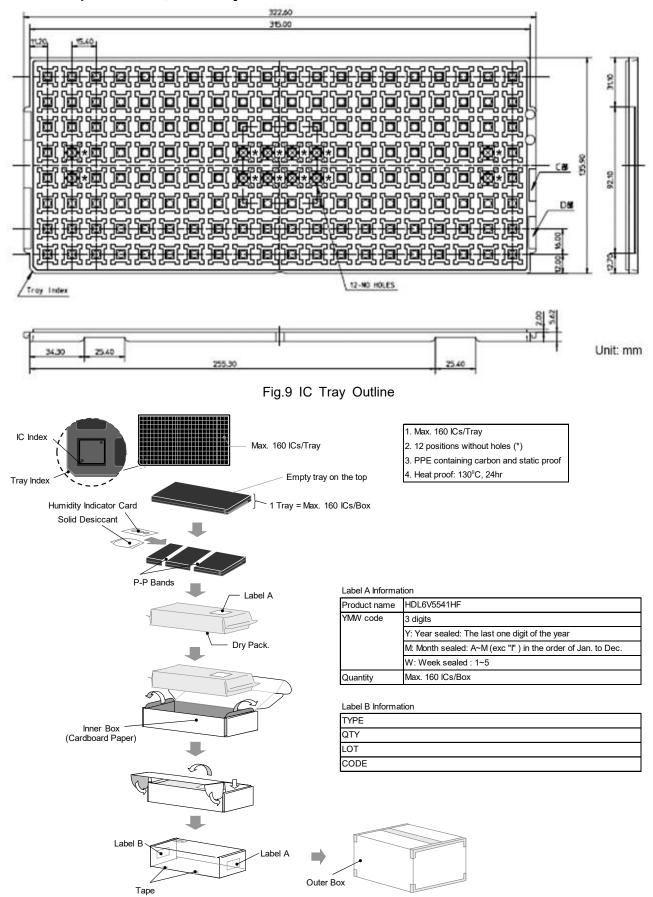


Fig.10 Transport Media, Quantity

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11. Mounting, Storage

11.1 Mounting Pad Design Example

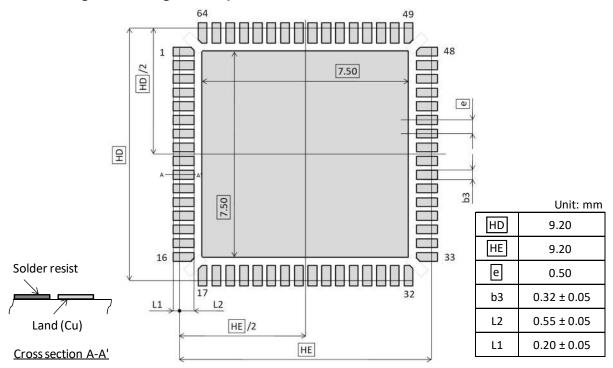


Fig.11 Mounting Pad Design Example

11.2 Storage Conditions

- 11.2.1 The storage location should be kept at 5 to 35 °C and 40 to 70% relative humidity. Keeping in a dry box is recommended. Moisture-proof property is assured for 12 months from delivery date for sealed moisture-proof packing, while it is guaranteed for 7 days from unpacked date under the condition above.
- 11.2.2 When the storage conditions do not conform to those above or other conditions occur indicating moisture exposure, the ICs should be dried to avoid package cracks. A baking process at 125 °C lasting for 24 hours results in sufficient dehumidification. The baking is not allowed more than twice, and the ICs should be mounted within 7 days after initial baking or within 10 days of total exposure after the second dehumidification.

11.3 Reflow Conditions

Typical full heating methods such as Infrared (IR), Hot air, and N2 reflow process are applicable. IR/Air reflow heating conditions are shown below.

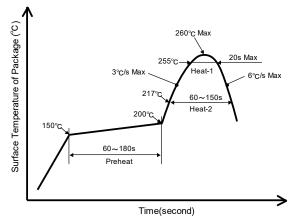


Fig.12 IR/Air Reflow Heating Conditions

12. Inspection

Hundred percent inspections shall be conducted on electrical characteristics.

13. Important Notice

- 13.1 ABLIC Inc. warrants performance of its hardware products (hereinafter called "products") to the specifications applicable at the time of sale in accordance with the Product Specification. Testing and other quality control techniques are utilized to the extent ABLIC Inc. needs to meet specifications described in the Product Specification. Specific testing of all parameters of each device is not necessarily performed, except those mandated by related laws and/or regulations.
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14. Cautions

- 14.1 Customers are advised to follow the cautions below to protect products from damage caused by electrical static discharge (ESD).
 - 14.1.1 Material of container or any device to carry products should be free from ESD, which may be caused by vibration while transportation. It is recommended that electric-conductive container or aluminum sheet be used as an effective countermeasure.
 - 14.1.2 Those what touch products such as work platform, machine, measurement/test equipment should be grounded.
 - 14.1.3 Those who deal with products should be grounded through a large series impedance around $100k\Omega$ to $1M\Omega$.
 - 14.1.4 Prevent friction with other materials made with high polymer.
 - 14.1.5 Prevent vibration or friction when carrying the printed circuit board (PCB) where products are mounted. To short circuit terminals is a recommended countermeasure to keep the same electric potential on the PCB.
 - 14.1.6 Avoid dealing with or storing products in an extremely arid environment.
- 14.2 "Absolute maximum ratings" should never be exceeded during use regardless of any change in external conditions. Otherwise, products may be damaged or destroyed. In no event shall ABLIC Inc. be liable for any failure in products or any secondary damage resulting from use at a value exceeding the absolute maximum ratings.
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- 14.4 Products may experience failures or malfunction in poor surroundings, such as electrical leakage in products due to long-term use in high humidity, malfunctioning or permanent damage due to chemical reaction of products in corrosive environment or due to discharge by strongly charged object near products or due to excessive mechanical shock. To use products in radiation environment is not assumed. To use products near material easy to ignite may cause a fire due to its flammable package. Avoid using products in such environment or take appropriate countermeasures depending on the environment.
- 14.5 Products are not designed, manufactured, or warranted to be suitable for use where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, life-support-related medical equipment, fuel control equipment and various kinds of safety equipment). Inclusion of products in such application shall be fully at the risk of customers. ABLIC Inc. assumes no liability for applications assistance, customer product design, or performance.

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- 6. When exporting the products, comply with the Foreign Exchange and Foreign Trade Act and all other export-related laws, and follow the required procedures.
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 - ABLIC Inc. is not liable for any losses, damages, claims or demands caused by unauthorized or unspecified use of the products.
- 9. In general, semiconductor products may fail or malfunction with some probability. The user of the products should therefore take responsibility to give thorough consideration to safety design including redundancy, fire spread prevention measures, and malfunction prevention to prevent accidents causing injury or death, fires and social damage, etc. that may ensue from the products' failure or malfunction.
 - The entire system in which the products are used must be sufficiently evaluated and judged whether the products are allowed to apply for the system on customer's own responsibility.
- 10. The products are not designed to be radiation-proof. The necessary radiation measures should be taken in the product design by the customer depending on the intended use.
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